30 JUL 2002

162162

PROCESS OF RECLAMATION OF SOI SUBSTRATE AND REPRODUCED SUBSTRATE

ABSTRACT OF THE DISCLOSURE

The preparation of an soi substrate yields a combination of a semiconductor base plate(2)and a single crystal semiconductor layer (4) with interposition of an insulating layer (3). The soi substrate is reclaimed through a first removal step of removing the single crystal semiconductor layer (4), and a second removal step of removing selectively the insulation layer (3). Thereby, the loss of the thickness of the base plate in the reclamation is decreased in the reproduction of the soi substrate.

Figure 2

G00002